



P-Ch 200V Fast Switching MOSFETs

Description

The HSH10P20 uses advanced trench MOSFET technology to provide excellent $R_{DS(ON)}$ and gate charge for use in a wide variety of other applications.

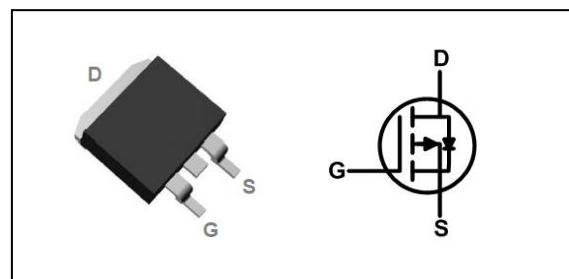
The HSH10P20 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

Product Summary

V_{DS}	-200	V
$R_{DS(ON),typ}$	650	mΩ
I_D	-10	A

TO-263 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-200	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-10	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-7.5	A
I_{DM}	Pulsed Drain Current ²	-40	A
EAS	Single Pulse Avalanche Energy ³	81	mJ
$P_D@T_C=25^{\circ}C$	Total Power Dissipation ⁴	80	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	1.6	°C/W



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-200	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-3A	---	650	810	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-2	---	-4	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-200V, V _{GS} =0V, T _J =25°C	---	---	-1	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ± 20V, V _{DS} =0V	---	---	± 100	nA
g _{fs}	Forward Transconductance	V _{DS} =-10V, I _D =-3A	---	5.5	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	5.4	---	Ω
Q _g	Total Gate Charge	V _{DS} =-50V, V _{GS} =-10V, I _D =-3A	---	82	---	nC
Q _{gs}	Gate-Source Charge		---	19	---	
Q _{gd}	Gate-Drain Charge		---	22	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-50V, V _{GS} =-10V, R _G =3.3Ω, I _D =-3A	---	18	---	ns
T _r	Rise Time		---	4.5	---	
T _{d(off)}	Turn-Off Delay Time		---	49.5	---	
T _f	Fall Time		---	28	---	
C _{iss}	Input Capacitance	V _{DS} =-25V, V _{GS} =0V, f=1MHz	---	2155	---	pF
C _{oss}	Output Capacitance		---	49	---	
C _{rss}	Reverse Transfer Capacitance		---	39	---	

Diode Characteristics

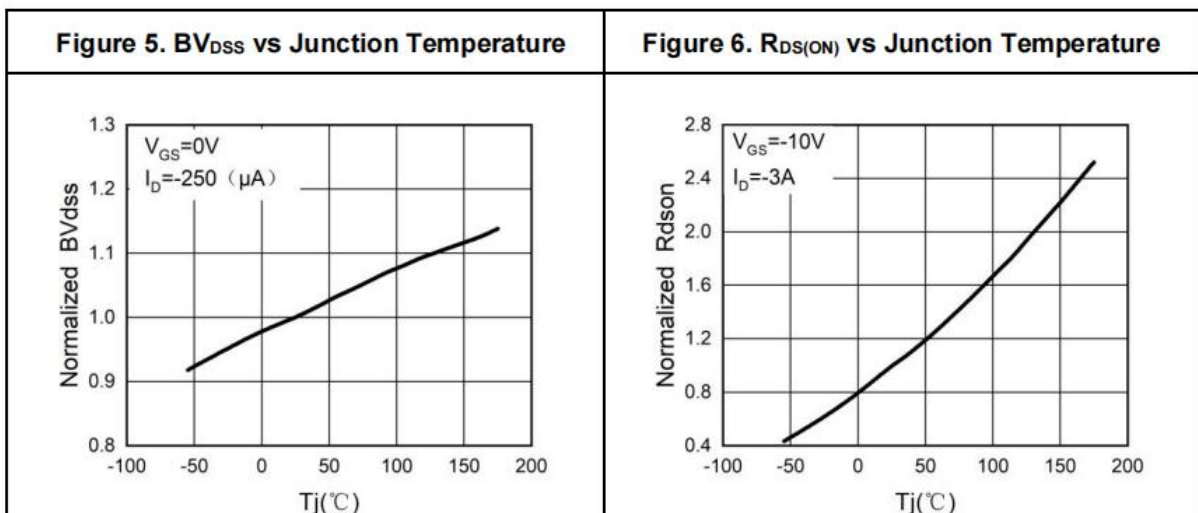
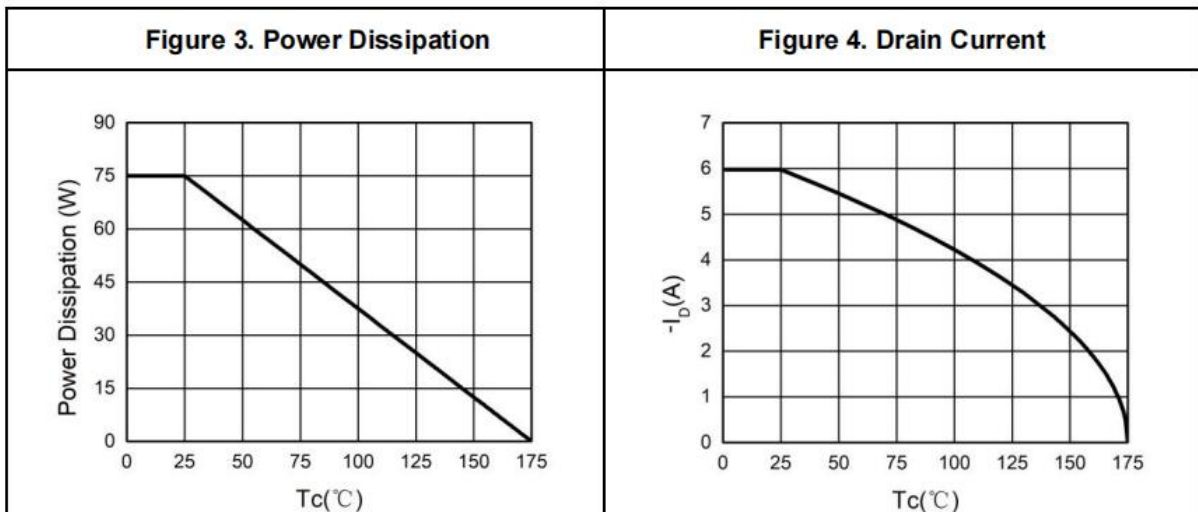
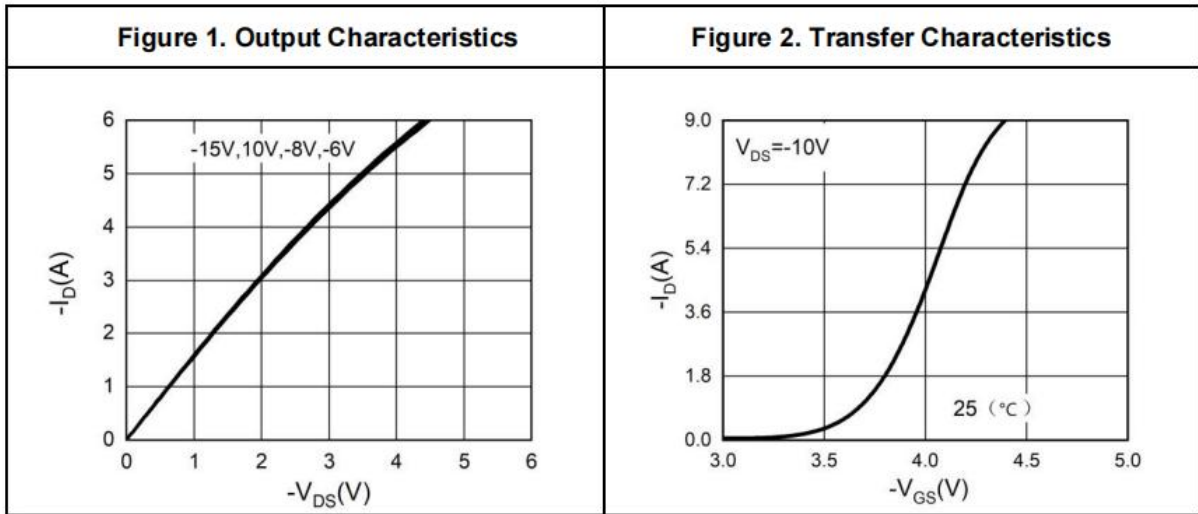
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	-10	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1.2	V
t _{rr}	Reverse Recovery Time	I _F =-3A, dI/dt=-100A/μs,	---	63	---	nS
Q _{rr}	Reverse Recovery Charge	T _J =25°C	---	195	---	nC

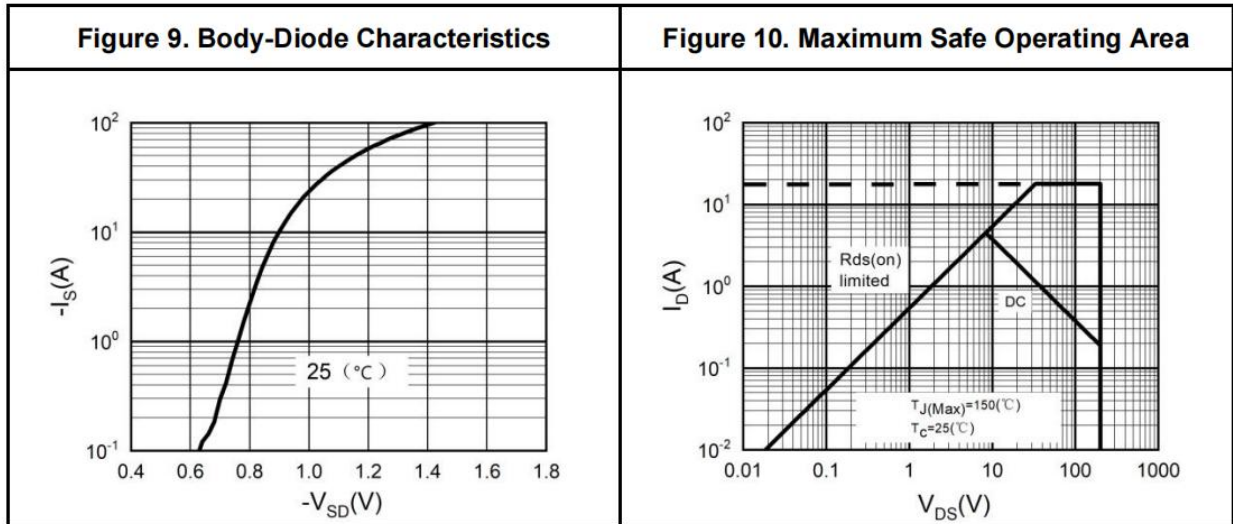
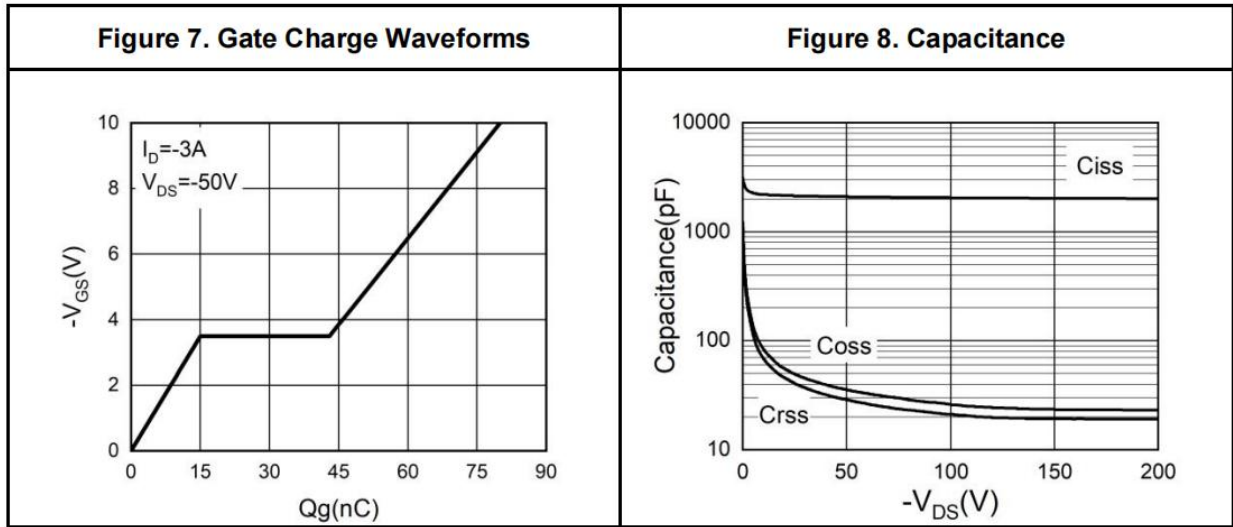
Note :

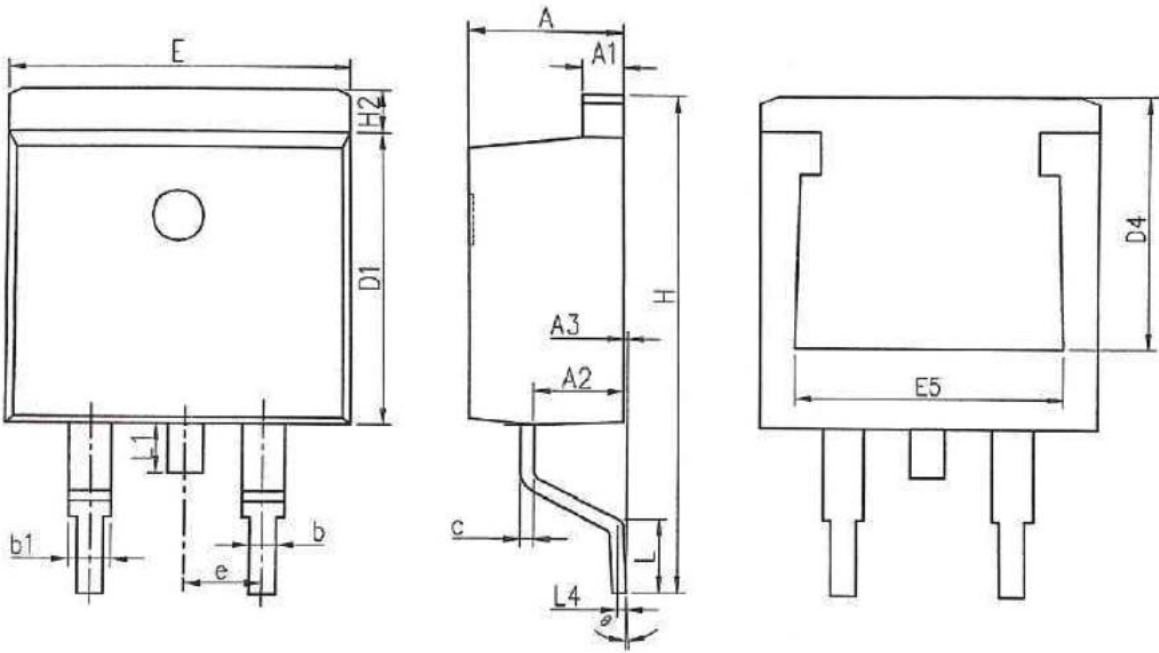
- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics







SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.370	4.770	0.172	0.188
A1	1.220	1.420	0.048	0.056
A2	2.200	2.890	0.087	0.114
A3	0.000	0.250	0.000	0.010
b	0.700	0.960	0.028	0.038
b1	1.170	1.470	0.046	0.058
c	0.300	0.530	0.012	0.021
D1	8.500	9.300	0.335	0.366
D4	6.600	-	0.260	-
E	9.860	10.36	0.388	0.408
E5	7.060	-	0.278	-
e	2.540 BSC		0.100 BSC	
H	14.70	15.70	0.579	0.618
H2	1.070	1.470	0.042	0.058
L	2.000	2.600	0.079	0.102
L1	1.400	1.750	0.055	0.069
L4	0.250 BSC		0.010 BSC	
Θ	0°	9°	0°	9°